

◆ **Features:**

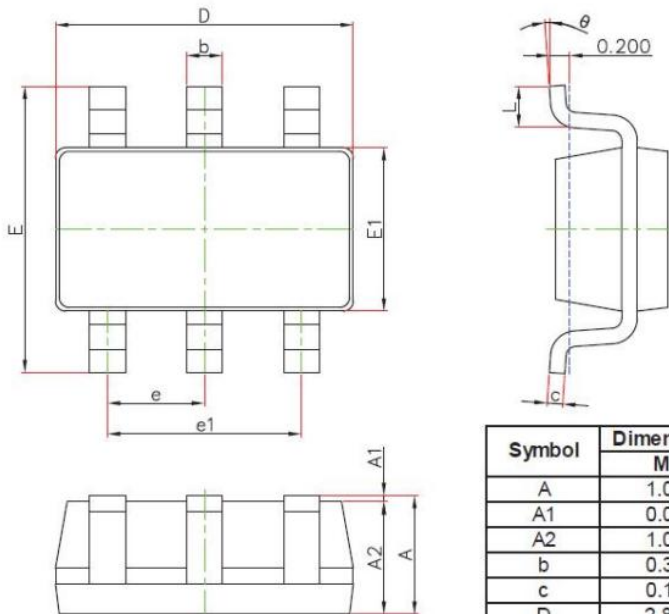
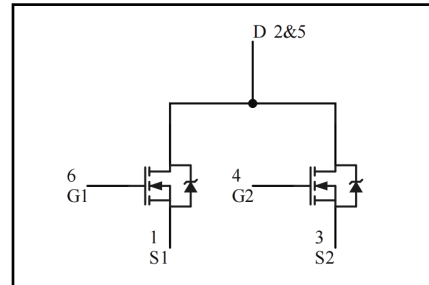
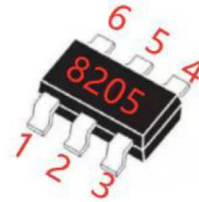
- ◇ Fast switching speed  
开关速度快
- ◇ High input impedance and low level drive  
高输入阻抗和低电平驱动
- ◇ Improved dv/dt capability, high ruggedness  
提高 dv/dt 能力, 高耐用性

◆ **Applications**

- ◇ High efficiency switch mode power supplies  
高效率开关电源
- ◇ Power factor correction  
功率因数校正
- ◇ Electronic lamp ballast  
电子整流器



**SOT-23-6**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
K	0°	8°	0°	8°

**◆ Absolute Maximum Ratings (Tc=25°C)**

Symbol	Parameters	Ratings	Unit
V <sub>DSS</sub>	Drain-Source Voltage 漏源电压	<b>20</b>	V
V <sub>GS</sub>	Gate-Source Voltage-Continuous 栅源电压	<b>±12</b>	V
I <sub>D</sub>	Drain Current-Continuous (Note 2) 漏极持续电流	<b>5</b>	A
I <sub>DM</sub>	Drain Current-Single Plused (Note 1) 漏极单次脉冲电流	<b>20</b>	A
P <sub>D</sub>	Power Dissipation (Note 2) 功率损耗	<b>1.5</b>	W
T <sub>j</sub>	Max.Operating junction temperature 最大结温	<b>150</b>	°C

**◆ Electrical characteristics (Tc=25°C unless otherwise noted)**

Symbol	Parameters	Min	Typ	Max	Units	Conditions
<b>Static Characteristics</b>						
B <sub>V</sub> DSS	Drain-Source Breakdown VoltageCurrent (Note 1) 漏极击穿电压	<b>20</b>	--	--	V	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C
V <sub>GS(th)</sub>	Gate Threshold Voltage 栅极开启电压	<b>0.40</b>	<b>0.62</b>	<b>1.00</b>	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
R <sub>DS(on)</sub>	Drain-Source On-Resistance 漏源导通电阻	--	<b>14.5</b>	<b>20</b>	mΩ	V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A
I <sub>GSS</sub>	Gate-Body Leakage Current 栅极漏电流	--	--	<b>±100</b>	nA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0
I <sub>DSS</sub>	Zero Gate Voltage Drain Current 零栅极电压漏极电流	--	--	<b>1</b>	μA	V <sub>DS</sub> =30V, V <sub>GS</sub> =0
g <sub>fs</sub>	Forward Transconductance 正向跨导	--	<b>5</b>	--	S	V <sub>DS</sub> =5V, I <sub>D</sub> =2A

Switching Characteristics						
$T_{d(on)}$	Turn-On Delay Time 开启延迟时间	--	3.5	--	ns	$V_{DS}=10V, I_D=5A,$ $R_G=2.7\Omega, V_{GS}=5V$ (Note 2)
$T_r$	Rise Time 上升时间	--	2.5	--	ns	
$T_{d(off)}$	Turn-Off Delay Time 关闭延迟时间	--	20	--	ns	
$T_f$	Fall Time 下降时间	--	7.5	--	ns	
$Q_g$	Total Gate Charge 栅极总电荷	--	8.2	--	nC	$V_{DS}=10V, V_{GS}=5V$ $I_D=5A$ (Note 2)
$Q_{gs}$	Gate-Source Charge 栅源极电荷	--	1.0	--	nC	
$Q_{gd}$	Gate-Drain Charge 栅漏极电荷	--	1.5	--	nC	
Dynamic Characteristics						
$C_{iss}$	Input Capacitance 输入电容	--	350	--	pF	$V_{DS}=20V, V_{GS}=0,$ $f=1MHz$
$C_{oss}$	Output Capacitance 输出电容	--	75	-	pF	
$C_{rss}$	Reverse Transfer Capacitance 反向传输电容	--	75	--	pF	
$I_S$	Continuous Drain-Source Diode Forward Current (Note 2) 二极管导通正向持续电流	--	--	5.0	A	
$V_{SD}$	Diode Forward On-Voltage 二极管正向导通电压	--	--	1.0	V	$I_S=1A, V_{GS}=0$
$R_{th(j-c)}$	Thermal Resistance, Junction to Case 结到外壳的热阻	--	--	83.3	$^{\circ}C/W$	

Note 1: Repetitive Rating : Pulse width limited by maximum junction temperature

Note 2: Pulse test: PW  $\leq$  300us , duty cycle  $\leq$  2%.